

In the Claims:

1. (once amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,  
wherein said wafer includes an area in which crystal originated particles are generated,  
wherein a surface density of particles having a particle size of not less than  $0.12\ \mu\text{m}$  on the wafer surface is not more than  $15\ \text{counts}/\text{cm}^2$ , even after repeating the a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing  $\text{NH}_4\text{OH}$ ,  $\text{H}_2\text{O}_2$ , and  $\text{H}_2\text{O}$ .
2. (original) A silicon single crystal wafer for a particle monitor according to Claim 1, wherein said wafer has an oxygen concentration of not more than  $13 \times 10^{17}\ \text{atoms}/\text{cm}^3$  (old ASTM).
3. (once amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,  
wherein said wafer includes an area in which crystal originated particles are generated, and further said silicon single crystal ingot has a nitrogen concentration of  $1 \times 10^{13} - 1 \times 10^{15}\ \text{atoms}/\text{cm}^3$ ,  
wherein a surface density of particles having a particle size of not less than  $0.12\ \mu\text{m}$  on the wafer surface is not more than  $1\ \text{count}/\text{cm}^2$ , even after repeating the a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing  $\text{NH}_4\text{OH}$ ,  $\text{H}_2\text{O}_2$ , and  $\text{H}_2\text{O}$ .
4. (original) A silicon single crystal wafer for a particle monitor according to Claim 3, wherein said wafer has an oxygen concentration of not more than  $13 \times 10^{17}\ \text{atoms}/\text{cm}^3$  (old ASTM).
5. (once amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein, in said Czochralski method, the time period of passing the temperature range from 1150°C to 1070°C is within 20 min and the time period of passing the temperature range from 900°C to 800°C is within 40 min,

wherein a surface density of particles having a particle size of not less than 0.12  $\mu\text{m}$  on the wafer surface is not more than 15 counts/ $\text{cm}^2$ , even after repeating the a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing  $\text{NH}_4\text{OH}$ ,  $\text{H}_2\text{O}_2$ , and  $\text{H}_2\text{O}$ .

6. (original) A silicon single crystal wafer for a particle monitor according to Claim 5, wherein said wafer has an oxygen concentration of not more than  $13 \times 10^{17}$  atoms/ $\text{cm}^3$  (old ASTM).

7. (once amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein, in said Czochralski method, the time period of passing the temperature range from 1150°C to 1070°C is within 20 min and the time period of passing the temperature range from 900°C to 800°C is within 40 min,

wherein said silicon single crystal ingot has a nitrogen concentration of  $1 \times 10^{13} - 1 \times 10^{15}$  atoms/ $\text{cm}^3$ ,

wherein a surface density of particles having a particle size of not less than 0.12  $\mu\text{m}$  on the wafer surface is not more than 1 count/ $\text{cm}^2$ , even after repeating the a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing  $\text{NH}_4\text{OH}$ ,  $\text{H}_2\text{O}_2$ , and  $\text{H}_2\text{O}$ .

8. (original) A silicon single crystal wafer for a particle monitor according to Claim 7, wherein said wafer has an oxygen concentration of not more than  $13 \times 10^{17}$  atoms/ $\text{cm}^3$  (old ASTM).

9. (once amended) A silicon single crystal wafer for a particle monitor according to ~~any one of~~ Claim 1, ~~3, 5 or 7~~, wherein, in said Standard Cleaning - 1, the a chemical component of the a used

solution is  $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$ , and the cleaning is repeated six times, and each cleaning is carried out for 10 min.

Please add new claims 10 – 12.

10. (new) A silicon single crystal wafer for a particle monitor according to Claim 3, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is  $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$ , the cleaning is repeated six times, and each cleaning is carried out for 10 min.

11. (new) A silicon single crystal wafer for a particle monitor according to Claim 5, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is  $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$ , the cleaning is repeated six times, and each cleaning is carried out for 10 min.

12. (new) A silicon single crystal wafer for a particle monitor according to Claim 7, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is  $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$ , the cleaning is repeated six times, and each cleaning is carried out for 10 min.